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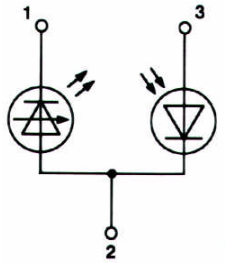
RLT6505G TECHNICAL DATA

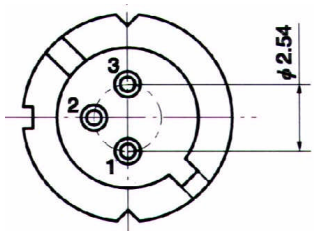
Visible Wavelength Laserdiode

Structure: **AlGaInP, index guided, single transverse mode**
Lasing wavelength: **650 nm**
Max. optical power: **5 mW**
Package: **9 mm G or 5.6mm MG**

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	5	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operation Case Temperature	T_C	-10 .. +40	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	kink free			5	mW
Threshold Current	I_{th}		20	30	40	mA
Operation Current	I_{op}	P_o =5mW		45	70	mA
Operating Voltage	V_{op}	P_o =5mW		2.2	2.7	V
Lasing Wavelength	l_p	P_o =5mW		650	655	nm
Beam Divergence	q_1	P_o =5mW	5	8	11	°
Beam Divergence	q_2	P_o =5mW	25	31	37	°
Astigmatism	As	P_o =5mW, NA=0.4		11		µm
Monitor Current	I_m	P_o =5mW, V_r=5V		10		µA